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PMN40UPE

20 V, single P-channel Trench MOSFET 13 August 2012

Product data sheet

1. **Product profile**

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Fast switching
- Trench MOSFET technology
- 4 kV ESD protection

1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-6	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -3 A; T_j = 25 °C		-	37	43	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D I
2	D	drain		
3	G	gate	<u>0</u> 1 1 2 3	G T
4	S	source	TSOP6 (SOT457)	
5	D	drain		
6	D	drain		S 017aaa259

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMN40UPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457		

4. Marking

Table 4. Marking codes

Type number	Marking code
PMN40UPE	WD

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-6	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-4.7	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-3.5	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-16	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	500	mW
			[1]	-	1220	mW
		T _{sp} = 25 °C		-	8330	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.3	Α
ESD maximum rating						
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	4000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

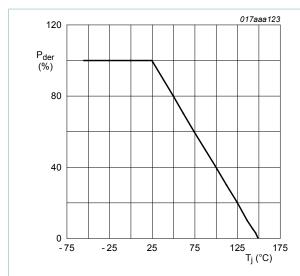


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

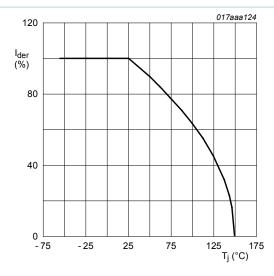


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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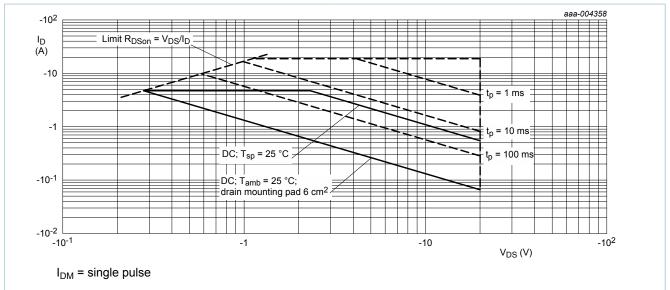


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uig-a)	thermal resistance		[1]	-	216	250	K/W
	from junction to		<u>[2]</u>	-	83	95	K/W
	ambient	in free air; t ≤ 5 s	<u>[2]</u>	-	51	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	10	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

Product data sheet

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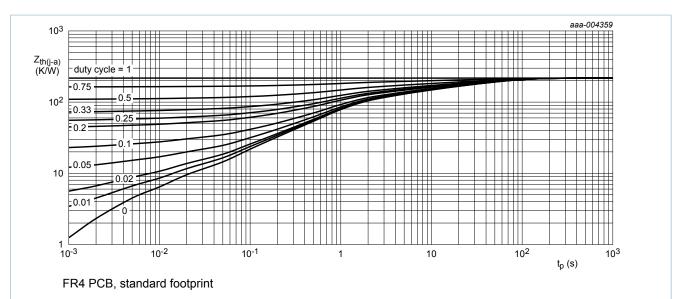


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

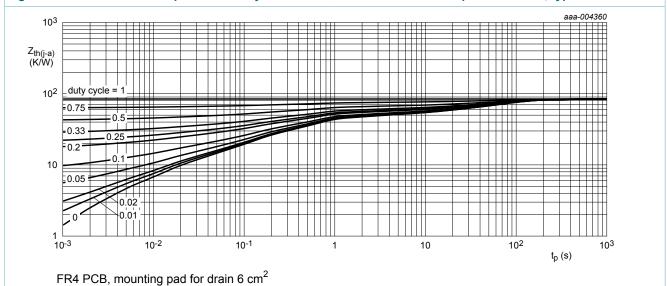


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _{amb} = 150 °C	-	-	-15	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -3 A; T_j = 25 °C	-	37	43	mΩ
	resistance	V_{GS} = -4.5 V; I_D = -3 A; T_j = 150 °C	-	51	59	mΩ
		V_{GS} = -2.5 V; I_D = -3 A; T_j = 25 °C	-	45	55	mΩ
		V_{GS} = -1.8 V; I_D = -3 A; T_j = 25 °C	-	59	72	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -4 A; T_{j} = 25 °C	-	15	-	S
Dynamic cl	haracteristics					,
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -4.4 A; V_{GS} = -4.5 V; I_{j} = 25 °C	-	15.6	23	nC
Q_{GS}	gate-source charge		-	2.5	-	nC
Q_{GD}	gate-drain charge		-	2.8	-	nC
C _{iss}	input capacitance	V_{DS} = -10 V; f = 1 MHz; V_{GS} = 0 V;	-	1820	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	207	-	pF
C _{rss}	reverse transfer capacitance		-	146	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -4 A; V_{GS} = -4.5 V;	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	21	-	ns
t _{d(off)}	turn-off delay time		-	50	-	ns
t _f	fall time		-	34	-	ns
Source-dra	in diode		I		1	
V_{SD}	source-drain voltage	$I_S = -1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	-0.7	-1.2	V

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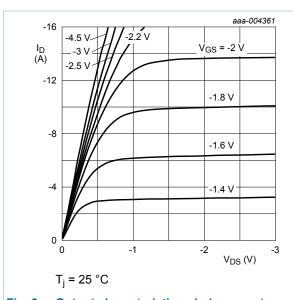
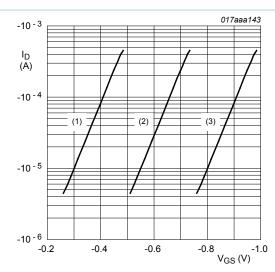


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_j$$
 = 25 °C; V_{DS} = -3 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

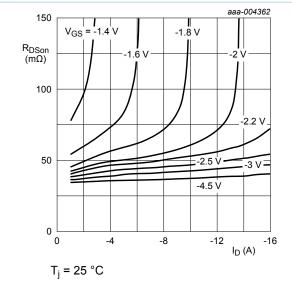


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

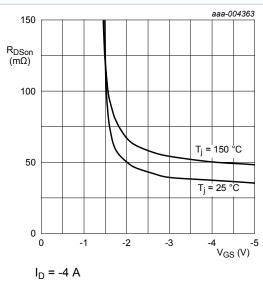


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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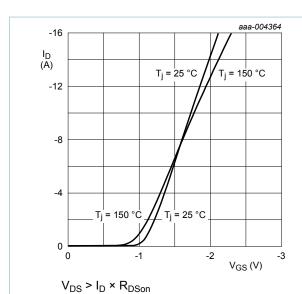


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

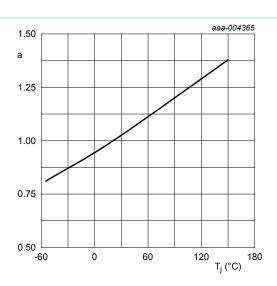


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

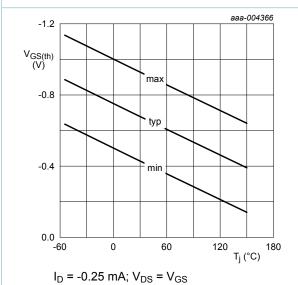
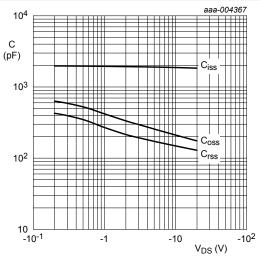


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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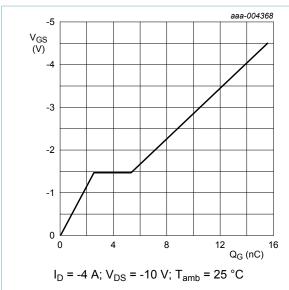


Fig. 14. Gate-source voltage as a function of gate charge; typical values

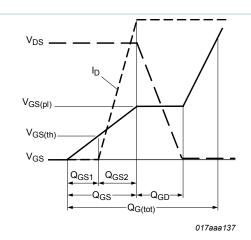


Fig. 15. Gate charge waveform definitions

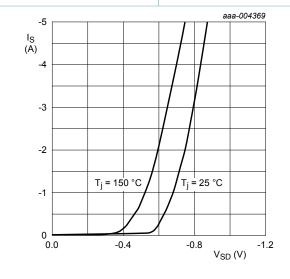
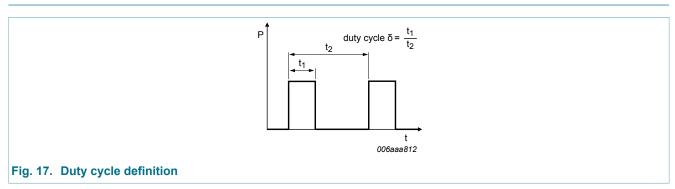


Fig. 16. Source current as a function of source-drain voltage; typical values

8. Test information

 $V_{GS} = 0 V$



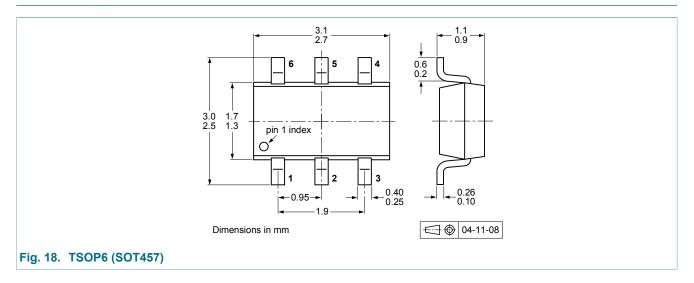
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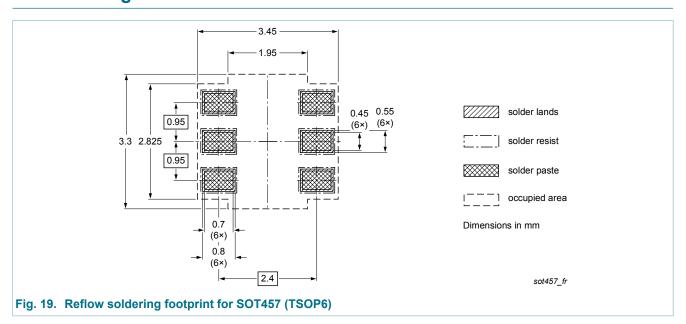
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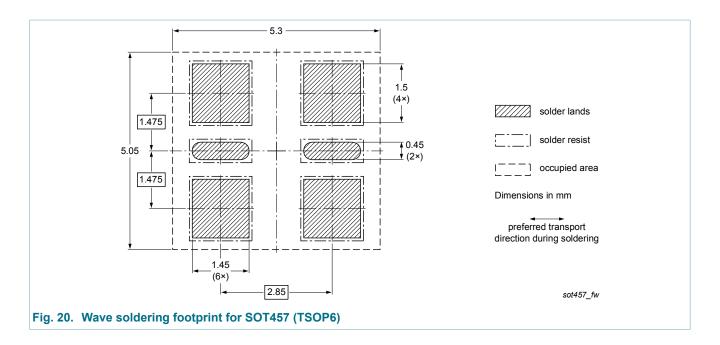
9. Package outline



10. Soldering



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11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN40UPE v.1	20120813	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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